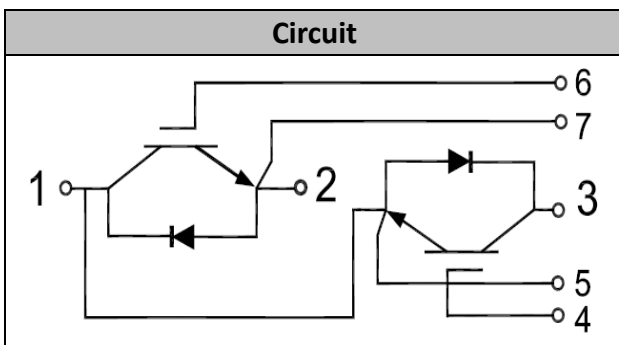


IGBT Modules

V_{CES}	1200V
I_c	200A

Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)
- Soft switching welding machine



Features

- Low $V_{CE(sat)}$ with Trench technology
- $V_{ce(sat)}$ with positive temperature coefficient
- High short circuit capability(10us)
- Including ultra fast & soft recovery anti-parallel FWD
- Low inductance
- Maximum junction temperature 175°C

● IGBT

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_c=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_c	$T_C=100^{\circ}C$	200	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	400	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	1250	W



Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=7.6mA, T_{vj}=25^{\circ}C$	5.0	5.8	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.85	2.50	V
		$I_C=200A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.20		
		$I_C=200A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.30		
Gate Charge	Q_G			1.2		uC
Internal Gate Resistor	R_{Gint}			3.8		Ω
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$		12.8		nF
Reverse Transfer Capacitance	C_{res}	$f=1MHz, T_{vj}=25^{\circ}C$		0.5		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=200A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=3.6\Omega$ $T_{vj}=25^{\circ}C$		187		ns
Rise Time	t_r			62		ns
Turn-off Delay Time	$t_{d(off)}$			266		ns
Fall Time	t_f			179		ns
Energy Dissipation During Turn-on Time	E_{on}			21.1		mJ
Energy Dissipation During Turn-off Time	E_{off}			12.9		mJ
Turn-on Delay Time	$t_{d(on)}$		$I_C=200A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=3.6\Omega$ $T_{vj}=150^{\circ}C$		192	
Rise Time	t_r			71		ns
Turn-off Delay Time	$t_{d(off)}$			311		ns
Fall Time	t_f			265		ns
Energy Dissipation During Turn-on Time	E_{on}			32.7		mJ
Energy Dissipation During Turn-off Time	E_{off}			17.8		mJ
SC Data	I_{sc}	$t_p \leq 10\mu s, V_{GE}=15V,$ $T_{vj}=150^{\circ}C, V_{CC}=900V,$ $V_{CEM} \leq 1200V$			800	



● Diode

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		200	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	400	A
I^2t -value	I^2t	$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=125^{\circ}\text{C}$	7550	A ² s
		$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	7100	

Characteristic Values

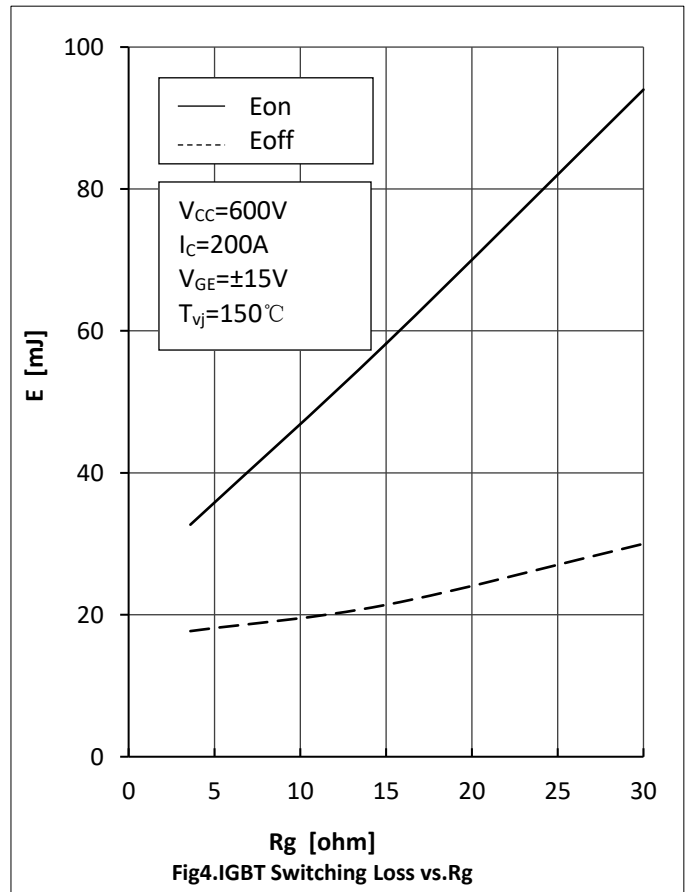
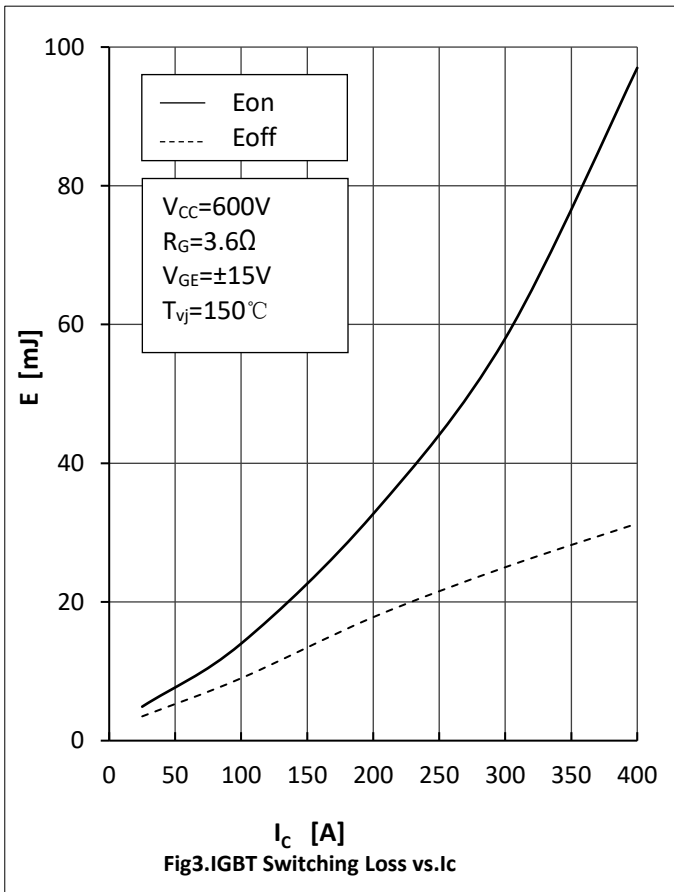
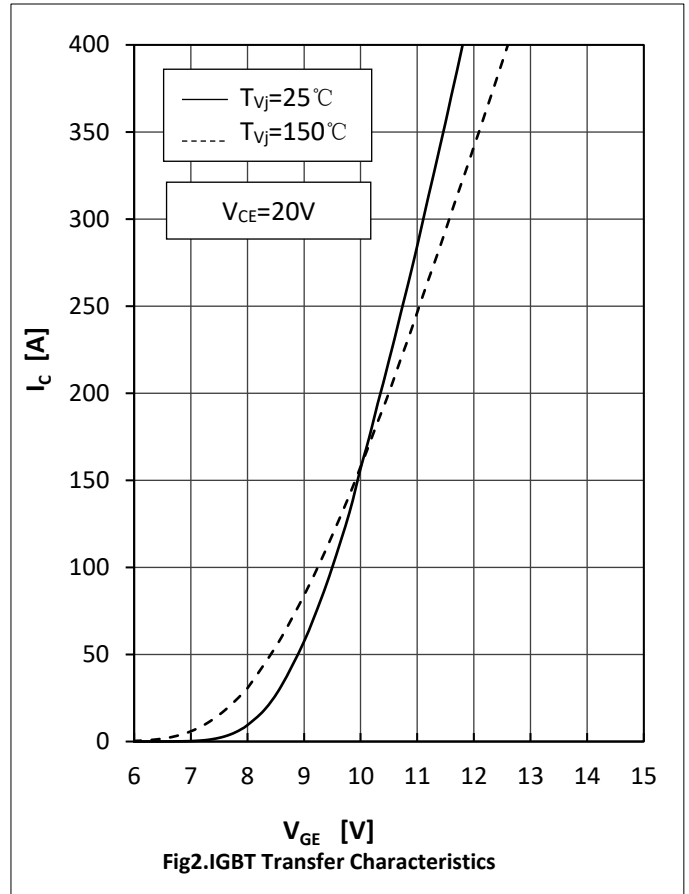
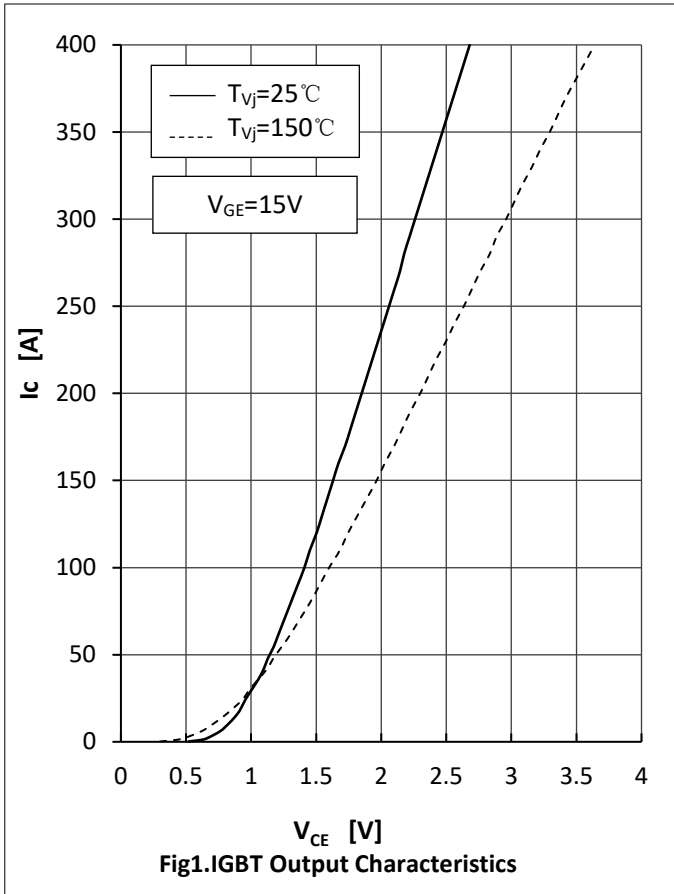
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=200\text{A}, T_{vj}=25^{\circ}\text{C}$		2.00	2.80	V
		$I_F=200\text{A}, T_{vj}=125^{\circ}\text{C}$		1.85		
		$I_F=200\text{A}, T_{vj}=150^{\circ}\text{C}$		1.80		
Recovered Charge	Q_{rr}	$I_F=200\text{A}$		13.0		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt = 2400\text{A}/\mu\text{s}$		86		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}\text{C}$		3.9		mJ
Recovered Charge	Q_{rr}	$I_F=200\text{A}$		39.2		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt = 2400\text{A}/\mu\text{s}$		137		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^{\circ}\text{C}$		13.1		mJ

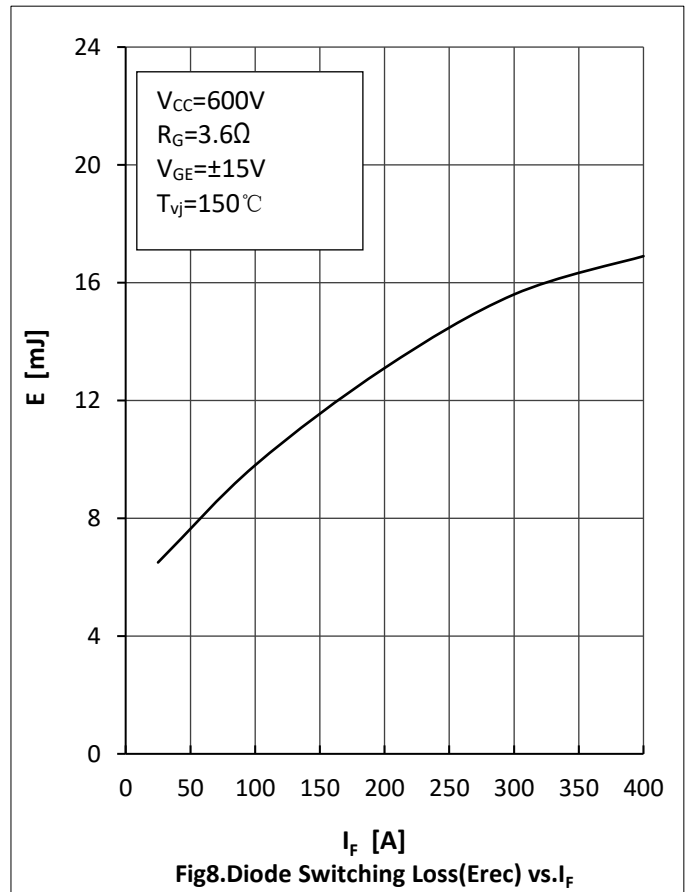
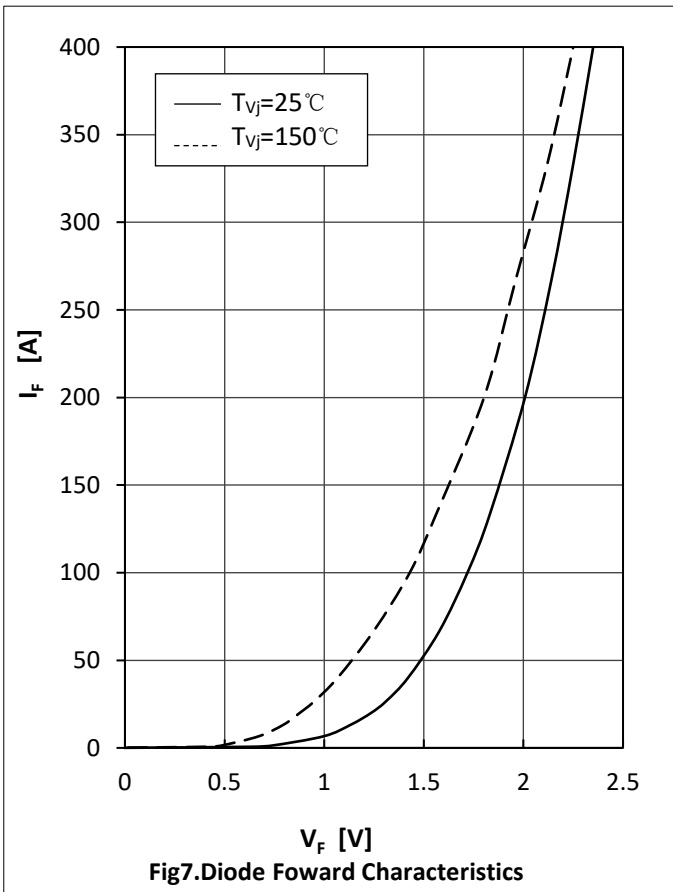
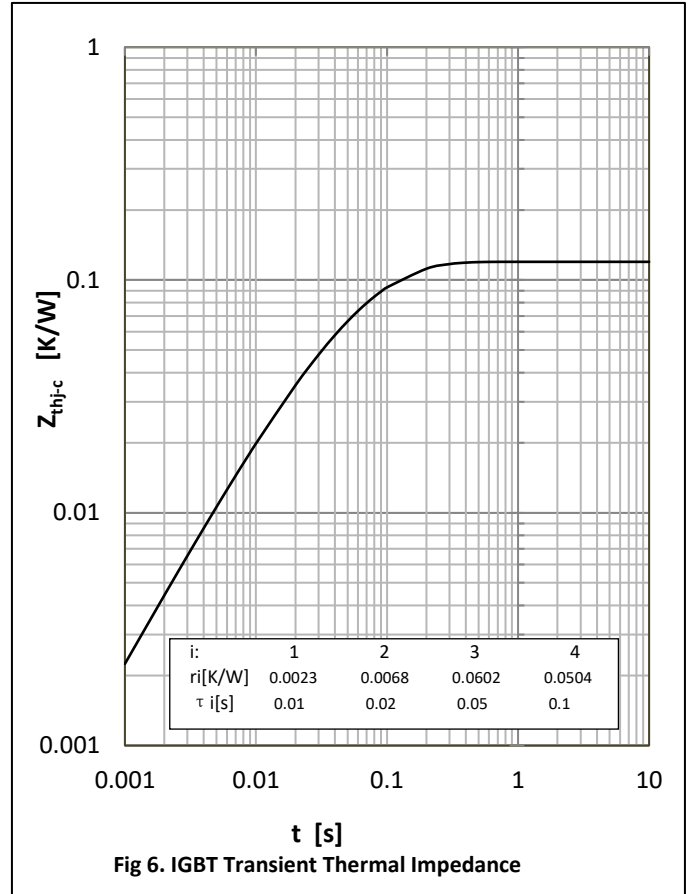
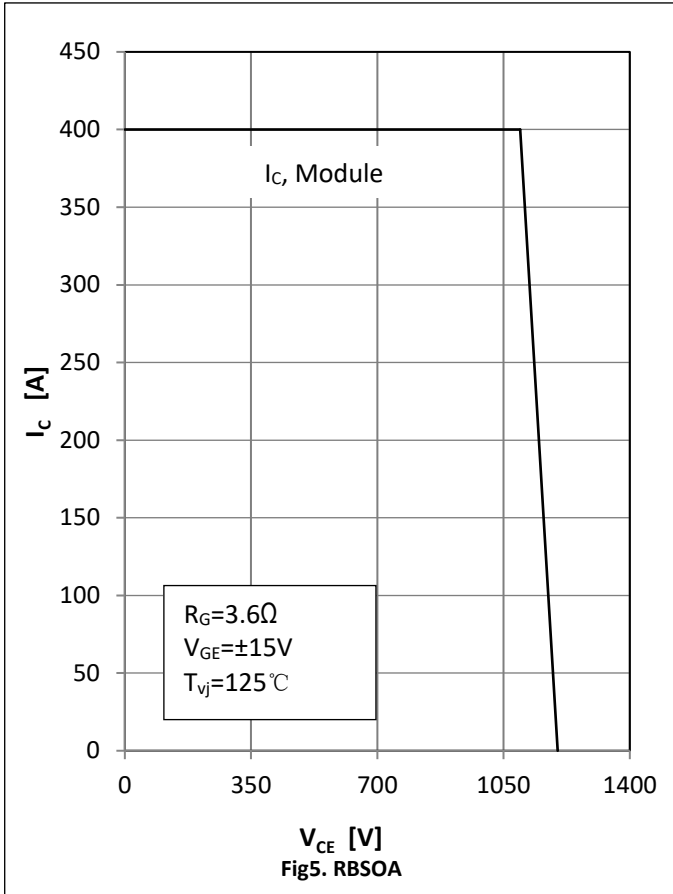


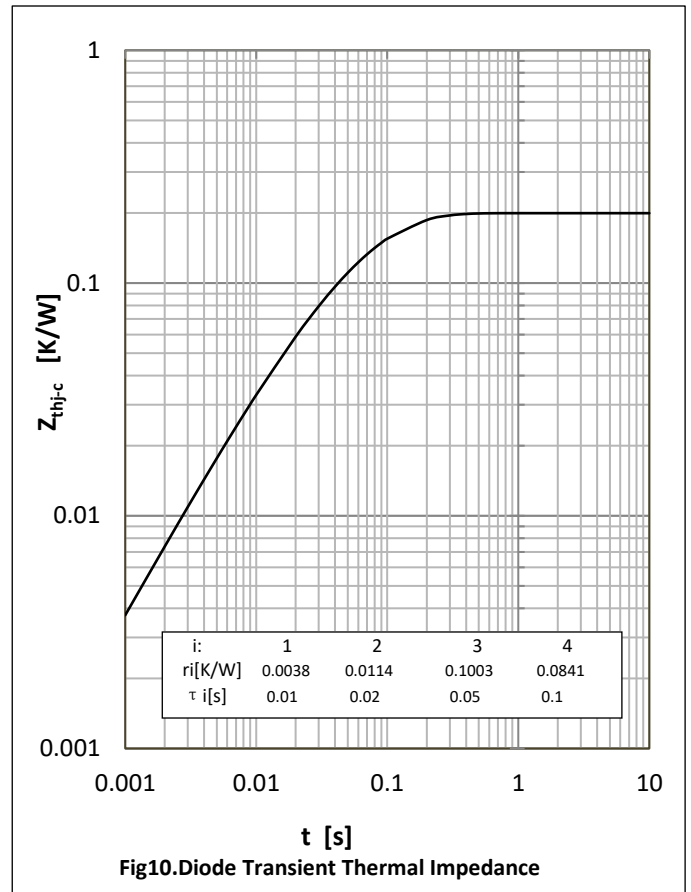
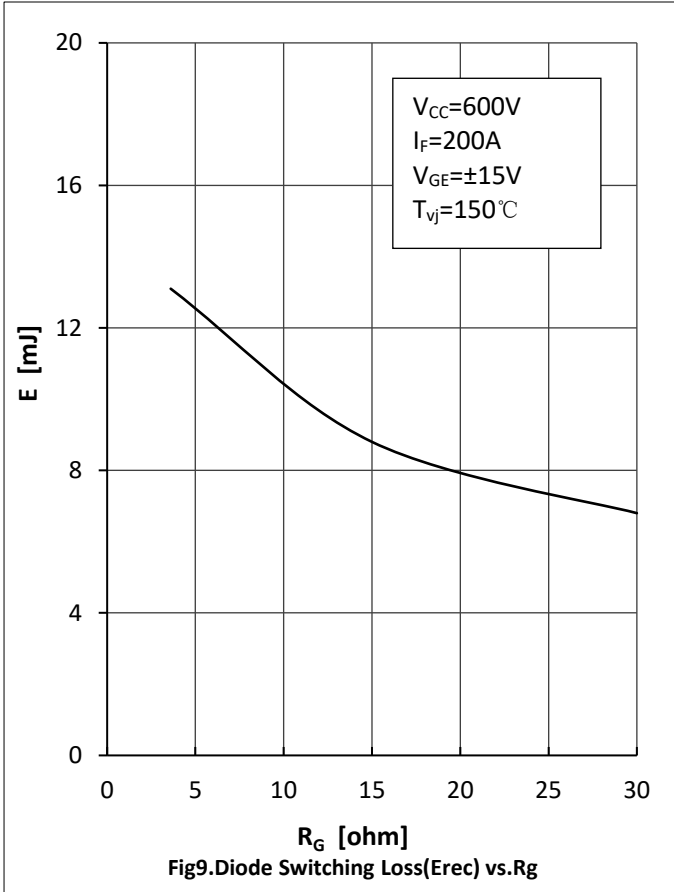
● Module Characteristics

T_c=25°C unless otherwise specified

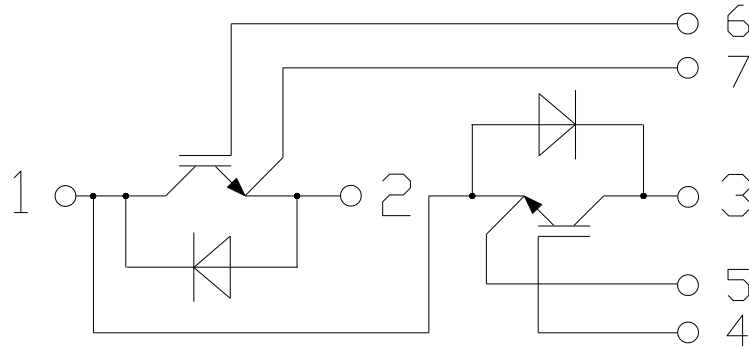
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V _{isol}	t=1min,f=50Hz	2500			V
Maximum Junction Temperature	T _{jmax}				175	°C
Operating Junction Temperature	T _{vj op}		-40		150	°C
Storage Temperature	T _{stg}		-40		125	°C
Thermal Resistance Junction-to Case	R _{θJC}	per IGBT			0.12	K/W
		per Diode			0.20	
Thermal Resistance Case-to Sink	R _{θCS}	Conductive grease applied		0.012	0.035	K/W
Comparative Tracking Index	CTI		400			
Module Electrodes Torque	M _t	Recommended(M6)	3.0		5.0	N·m
Module-to-Sink Torque	M _s	Recommended(M6)	3.0		5.0	N·m
Weight of Module	G			315		g





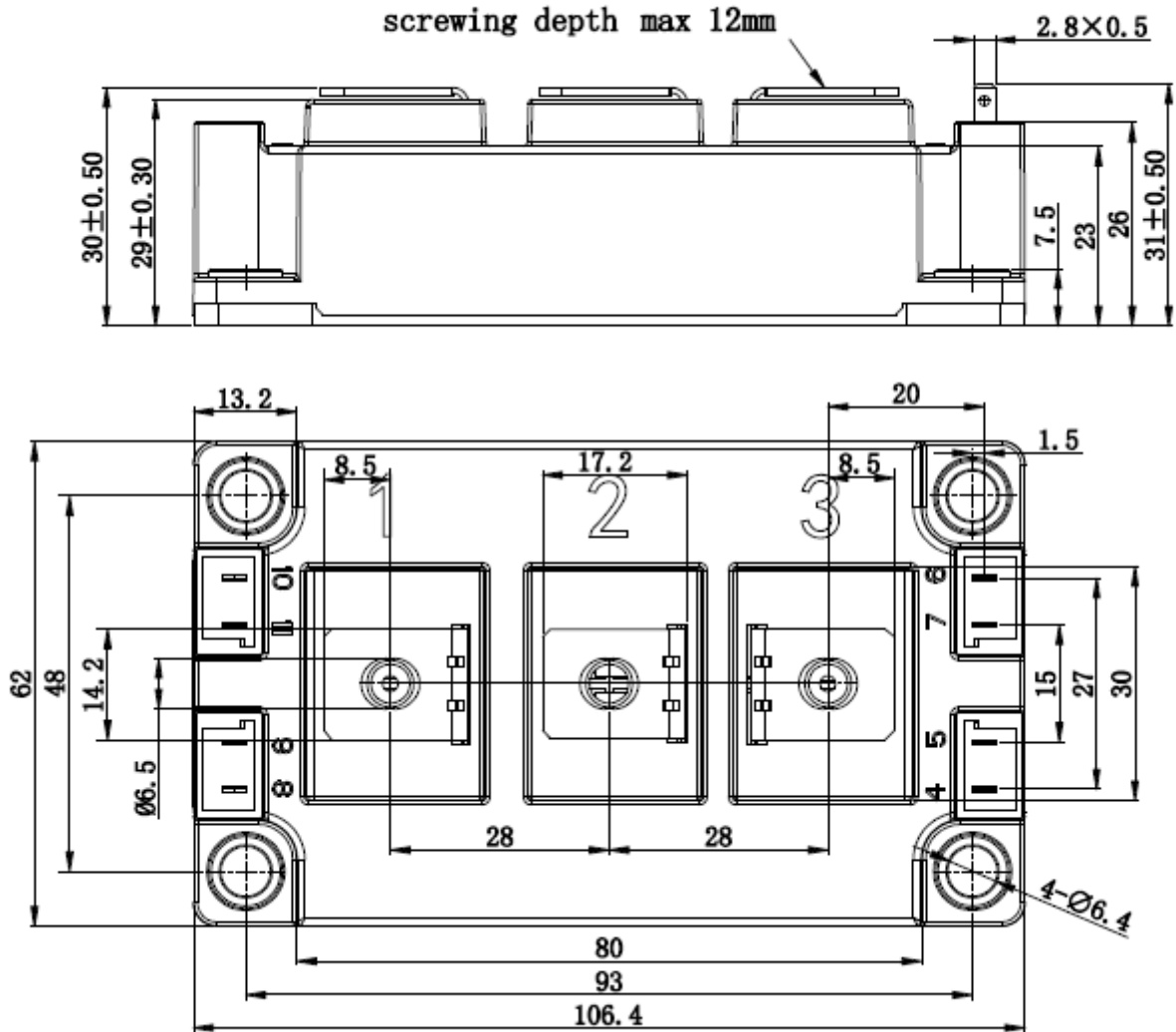


● **Circuit Diagram**



● **Package Outline Information**

Dimensions in Millimeters





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